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Inventor(s) : Seon Yong Cha
Issued : August 22, 2006
Title: MAGNETORESISTIVE RANDOM ACCESS MEMORY, AND MANUFACTURING METHOD THEREOF

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If a fee (currently \$100) was previously submitted for consideration of a Request for Certificate of Correction, under CFR 1.323, to correct assignment data, , no additional fee is required.

Magdalene Talley

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